

# DATA SHEET

## **PUMT1** Dual PNP transistor

Preliminary specification  
File under Discrete Semiconductors, SC04

1995 Dec 07

# Dual PNP transistor

# PUMT1

### FEATURES

- Two transistors in one SC70 package
- Reduces number of components and boardspace
- No mutual interference between the transistors.

### PINNING

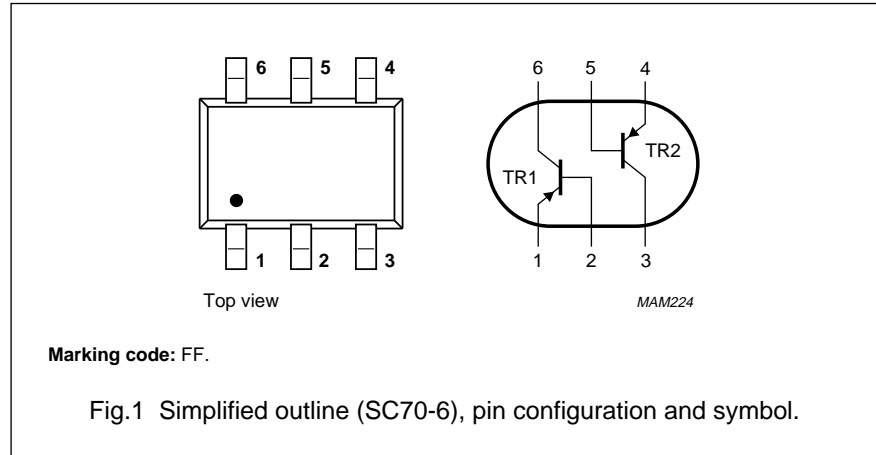
PIN	DESCRIPTION
1	emitter TR1
2	base TR1
3	collector TR2
4	emitter TR2
5	base TR2
6	collector TR1

### APPLICATIONS

- General purpose switching
- Small signal amplification.

### DESCRIPTION

Two PNP transistors in a plastic six lead SC70-6 (S-mini) package.



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	–50	V
$V_{CEO}$	collector-emitter voltage	open base	–	–40	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–100	mA
$h_{FE}$	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -6 \text{ V}$	120	–	
$f_T$	transition frequency	$I_C = -2 \text{ mA}; V_{CE} = -12 \text{ V}; f = 100 \text{ MHz}; T_{amb} = 25 \text{ }^\circ\text{C}$	100	–	MHz
<b>Per package</b>					
$P_{tot}$	total power dissipation	up to $T_{amb} = 25 \text{ }^\circ\text{C}$	–	300	mW

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	–50	V
$V_{CEO}$	collector-emitter voltage	open base	–	–40	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–100	mA
$P_{tot}$	total power dissipation		–	200	mW
$T_{amb}$	operating ambient temperature		–65	+150	°C
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
<b>Per package</b>					
$P_{tot}$	total power dissipation	up to $T_{amb} = 25\text{ °C}$ ; note 1	–	300	mW

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	416	K/W

**Note to the ‘Limiting values’ and ‘Thermal characteristics’**

- In accordance with standard mounting conditions SC70, six lead version.

**ELECTRICAL CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor</b>					
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = -50\ \mu\text{A}$ ; $I_E = 0$	–50	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = -1\ \text{mA}$ ; $I_B = 0$	–40	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = -50\ \mu\text{A}$ ; $I_C = 0$	–5	–	V
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -50\ \text{mA}$ ; $I_B = -5\ \text{mA}$ ; note 1	–	–200	mV
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -30\ \text{V}$ ; $I_E = 0$	–	–100	nA
		$V_{CB} = -30\ \text{V}$ ; $I_E = 0$ ; $T_j = 150\text{ °C}$	–	–10	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -4\ \text{V}$ ; $I_C = 0$	–	–100	nA
$h_{FE}$	DC current gain	$I_C = -1\ \text{mA}$ ; $V_{CE} = -6\ \text{V}$	120	–	
$f_T$	transition frequency	$I_C = -2\ \text{mA}$ ; $V_{CE} = -12\ \text{V}$ ; $f = 100\ \text{MHz}$	100	–	MHz
$C_c$	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -12\ \text{V}$ ; $f = 1\ \text{MHz}$	–	2.2	pF

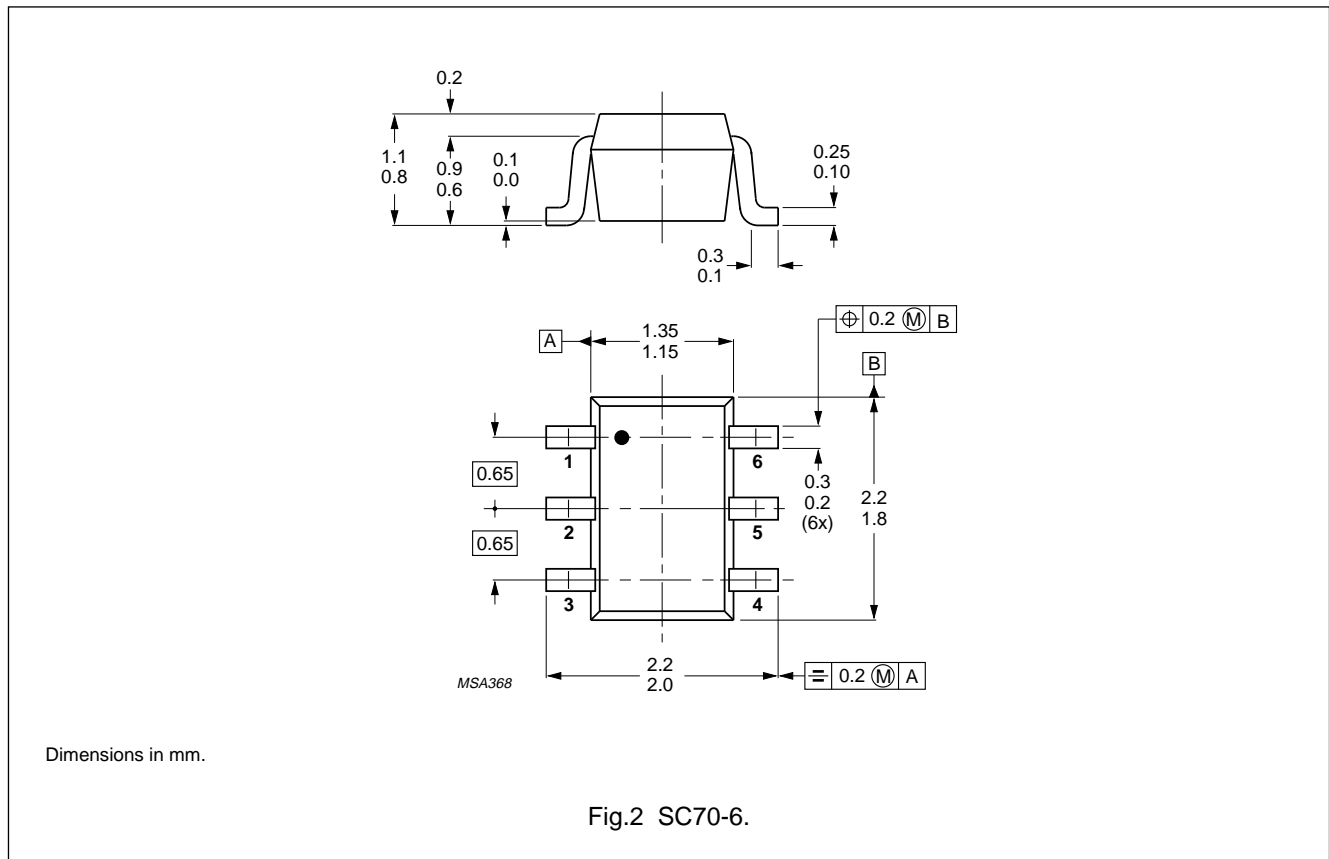
**Note to the ‘Electrical characteristics’**

- Pulse test:  $t_p \leq 300\ \mu\text{s}$ ;  $\delta \leq 0.02$ .

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PACKAGE OUTLINE



DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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**NOTES**

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**NOTES**

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